

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	("5481109").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 07:52
L3	71	(DGO Dual adj Gate adj Oxide) and (image imager imaging)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 08:04
L4	12	L3 and growing	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 07:52
L6	6	(DGO Dual adj Gate adj Oxide) and hideo near oi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 07:56
L7	273	(DGO Dual adj Gate adj Oxide) and oi not 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 07:57
L8	0	(Dual adj Gate adj Oxide) and oi not 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 07:57
L9	6	(Dual adj Gate adj Oxide) and oi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 07:57
L10	137	Dual adj Gate adj Oxide and growing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 07:59
L11	113	Dual adj Gate adj Oxide and growing with oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 07:59

## EAST Search History

L12	2	("6146795").PN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/09/11 08:05
L13	2	"6146795"	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:06
L14	987	chang.in. and cupertino.inci.	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:09
L15	111	14 and gate adj oxide	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:10
L16	125	chang.in. and Kuohua	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:09
L17	44	16 and gate adj oxide	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:11
L18	3	17 and logic and memory	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:10
L19	35	17 and (dual double two twice)	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:12
L20	33	17 and (dual double two twice) same gate	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:12
L21	24	17 and (dual double two twice) with gate	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:12
L22	7	16 and (dual double two twice) with gate adj oxide	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:15
L23	7	16 and (dual double two twice) with gate adj oxide and (growing forming depositing oxidizing)	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:16
L24	5	16 and (dual double two twice) with gate adj oxide and ((growing forming depositing) with oxide oxidizing)	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:19
L25	1	Huang with jiahua and (dual double two twice) with gate adj oxide and ((growing forming depositing) with oxide oxidizing)	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:19
L26	97	advanced adj micro adj devices and (dual double two twice) with gate adj oxide and ((growing forming depositing) with oxide oxidizing)	US-PGPUB; USPAT	OR	OFF	2006/09/11 08:20
L27	10	("4963501"   "5273926"   "5629548"   "5795803"   "5847432"   "5858827"   "5895954"   "5970331"   "5990516"   "6077736").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 09:24
L28	1	("6362049").PN.	DERWENT	OR	OFF	2006/09/11 09:55
L29	1	("6362049").PN.	USPAT	OR	OFF	2006/09/11 09:57

## EAST Search History

L30	12	pixel with (first gate (oxide or insulator) and second gate (oxide or insulator) or dgo or (twin or double or dual) gate (oxide or insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L31	708	(transfer transistor or TX) and (reset transistor or RX) and (drive transistor or DX or source follower) and (select transistor or SX)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L32	276	(transfer transistor or TX) and (reset transistor or RX) and (drive transistor or DX or source follower) and (select transistor or SX) and gate (oxide or dielectric or insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L33	214	L32 and peripheral	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L34	9	L33 and ("09941556" or "941556")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L35	7	peripheral with logic and (Ohkawa-Narumi or Mouli-Chandra or Rhodes-Howard)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L36	53	(transfer transistor or TX) and (reset transistor or RX) and (drive transistor or DX or source follower) and (select transistor or SX) and peripheral with logic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L37	37	L36 not ("09334261" or "334261" or "09686944" or "686944" or "09686944" or "686944")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56

## EAST Search History

L38	24	("3983395"   "4374700"   "4636829"   "4737852"   "5151385"   "5319604"   "5457433"   "5461425"   "5471515"   "5541402"   "5546205"   "5569616"   "5576763"   "5606295"   "5608243"   "5614744"   "5625210"   "5668613"   "5705846"   "5708263"   "5747840"   "5757045"   "5757453"   "5777701").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L39	11	("3623132"   "4093872"   "4155094"   "4287441"   "4309624"   "4683580"   "4859624"   "5184203"   "5192990"   "5198880"   "5323052").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L40	4	L38 and gate adj oxide	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/11 10:56
L41	27	"6100551"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/09/11 10:56
L42	1	"5471515".PN.	USPAT; USOCR	OR	OFF	2006/09/11 10:56
L43	6	(transfer (gate or transistor) or TX) and (reset (gate or transistor) or RX) and (drive transistor or DX or source follower) and (select transistor or SX) and ("09374990" or "374990")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L44	31	drive adj transistor same select adj transistor same transfer adj transistor same reset adj transistor and pixel and logic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 10:56
L45	51225	(etching etched etch) near3 (wet-etching hydrofluoric acid HF buffered adj oxide adj etchant BOE)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/11 10:56
L46	992	mask near (removing removal) with thinner sulfuric with plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/11 10:56

## EAST Search History

L47	19	cmos adj (image imager imaging) and (dual double) near3 (dielectric insulator insulating oxide insulated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/09/11 10:56
L48	1844	(438/57,87,275).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L49	170	CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L50	1	dual gate oxide and drive transistor and select transistor and transfer transistor and reset transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/11 10:56
L51	17	cmos adj (image imager imaging) and (dual double) near3 (dielectric insulator insulating oxide insulated)	US-PGPUB; USPAT	OR	ON	2006/09/11 10:56
L52	89	L49 and (field adj oxide fox)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L53	16	("4374700"   "5319604"   "5461425"   "5471515"   "5541402"   "5576763"   "5612799"   "5614744"   "5625210"   "5705846"   "5708263"   "5739562"   "5757045"   "6023081"   "6040593"   "6160282").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L54	88	"5614744" and oxide	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L55	50	"5614744" and (insulator oxide dielectric) near gate	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L56	11	(US-20020096733-\$).did. or (US-5625210-\$ or US-5841176-\$ or US-5933190-\$ or US-6204524-\$ or US-6326652-\$ or US-6333205-\$ or US-6376868-\$ or US-6445014-\$ or US-6617174-\$ or US-6740915-\$ or US-6835637-\$).did.	US-PGPUB; USPAT	OR	OFF	2006/09/11 10:56
L57	27	pixel and logic and (first gate (oxide or insulator) and second gate (oxide or insulator) or (twin or double or dual) gate (oxide or insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56

## EAST Search History

L58	181	drive same select same transfer same reset same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 10:56
L59	129	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGPUB; USPAT; USOCR	OR	OFF	2006/09/11 10:56
L60	153	hynix and (first gate (oxide or insulator) and second gate (oxide or insulator) or (twin or double or dual) gate (oxide or insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/11 10:56
L61	283	cmos and (DGO Dual adj Gate adj Oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 10:56